ABSTRACT

A semiconductor device includes a substrate, a SRAM cell including a pass-gate transistor, a pull-down transistor, and a pull-up transistor on substrate. The SRAM cell includes an active fin extending in a first direction, the pass-gate transistor and the pull-down transistor are disposed adjacent to each other on the active fin in the first direction, the pass-gate transistor includes first channel layers, a first gate electrode, first source/drain regions, and first inner spacers, the pull-down transistor includes second channel layers, a second gate electrode, second source/drain regions, and second inner spacers, and one of the first inner spacers and one of the second inner spacers are disposed on the same height level and have different thicknesses in the first direction.

FIG. 3B